

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
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ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	30	mA
				40	
I_H	$I_T=100mA$		MAX.	25	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150$		MIN.	1000	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150$		MIN.	5	A/ms
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	3	μs
t_{off}				30	

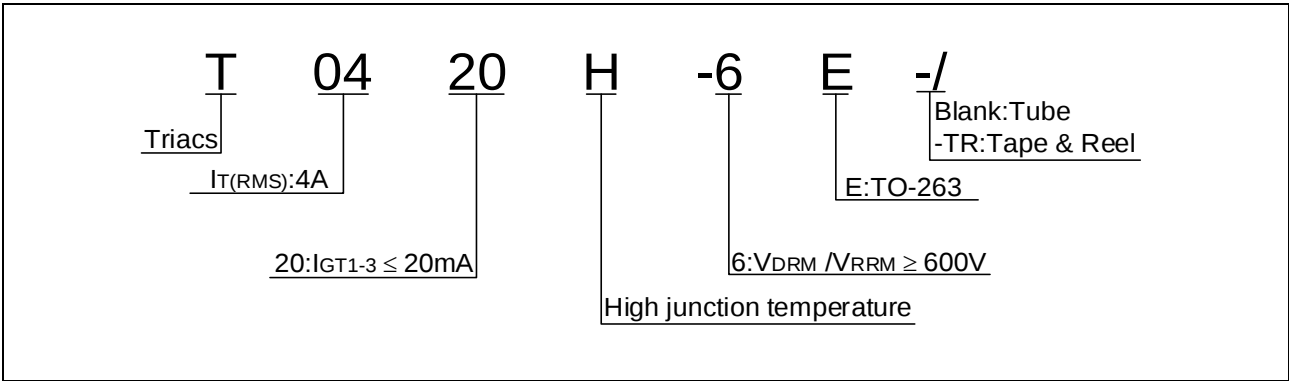
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5.5A$ $t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.6	V
R_D	Dynamic resistance	$T_j=150$	129	$m\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	0.8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.5	$^{\circ}W$
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=2cm^2$)	55	$^{\circ}W$

ORDERING INFORMATION



MARKING

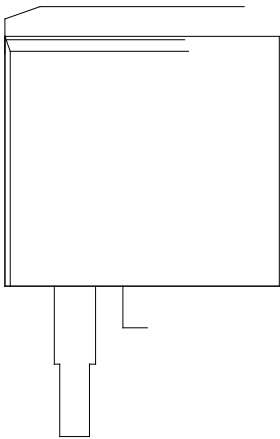
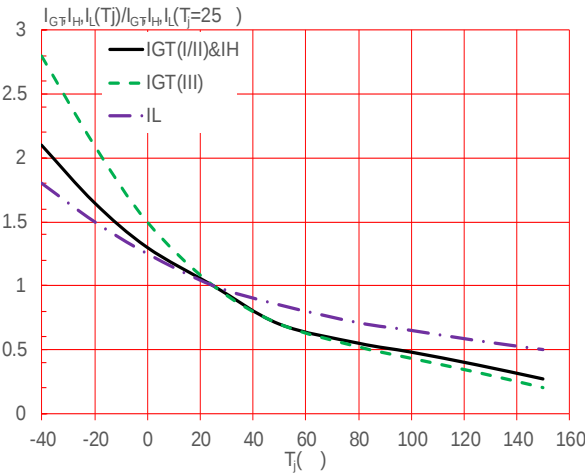
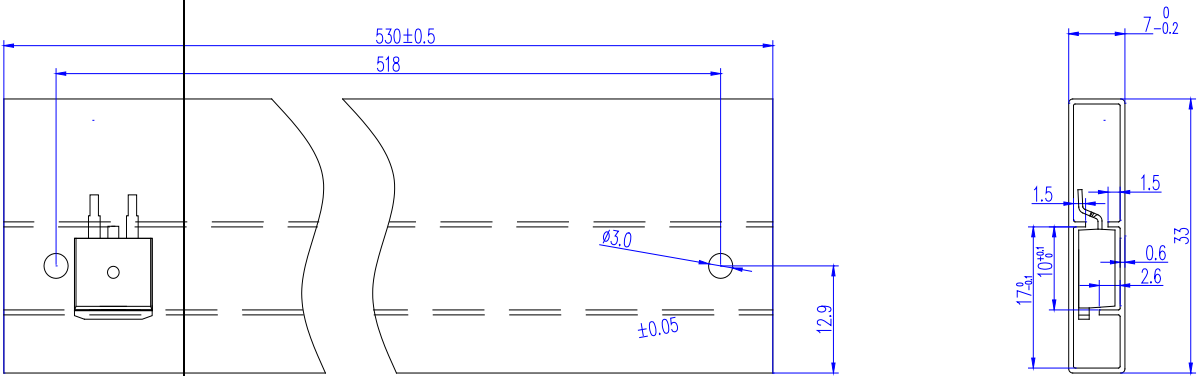


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
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